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Heat treatment of 6H-Silicon Carbide implanted with palladium at room temperature

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Abstract :

The Rutherford Backscattering Spectrometry (RBS) and Scanning Electron Microscopy (SEM) were used to investigate the effects of heat treatment of 6H-Silicon Carbide (6H-SiC) implanted with palladium (Pd) ions at a fluency of 2×10^{16} ions/cm² at room temperature. The implanted samples were then isochronally annealed for a period of 5 hour at a temperature range of 1000°C to 1400°C. The depth profile of the implanted samples before and after annealing was obtained using RBS. The microstructure and the topography of the samples were also investigated using the scanning electron microscopy (SEM) in order to investigate the effects of implanting the ions and annealing.

Award :

Yes

Level :

MSc

Supervisor :

C.C Theron Chris.theron@up.ac.za University of Pretoria

Paper :

No

Primary authors : Ms. KABINI, Jeaneth Thokozile (University of Pretoria)

Co-authors :

Presenter : Ms. KABINI, Jeaneth Thokozile (University of Pretoria)

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